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SHEET 1 OF 1

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ATTY. DOCKET NO.
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APPLICATION NO.
10/038,305

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

APPLICANT
Trivedi et al.

FILING DATE
January 2, 2002

GROUP
2818
3

(USE SEVERAL SHEETS IF NECESSARY)

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
TN	1.	4,804,560	2/14/89	Shioya et al.			
	2.	5,677,237	10/14/97	Tsai et al.			
	3.	5,714,804	2/3/98	Miller et al.			
TN	4.	5,840,625	11/24/98	Feldner			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
TN	5.	JP 8227939 Abstract	9/3/96	Japan			x	
TN	6.	JP 9532478 Abstract	2/21/95	Japan			x	

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

EXAMINER INITIAL		
TN	7.	Miller et al., "CVD Tungsten Interconnect and Contact Barrier Technology for VLSI," Solid State Technology, Dec. 1982, pp. 85-90.
TN	8.	Saraswat, et al. "Selective CVD of Tungsten for VLSI Technology," Journal of the Electrochemical Society, Vol. 131, No. 3, 1984, pp. 409-419.
TN	9.	Stacy et al. "Interfacial Structure of Tungsten Layers Formed by Selective Low Pressure Chemical Vapor Deposition," J. Electrochem. Soc.: Solid State Science and Technology, Vol. 132, No. 2, Feb. 1985, pp. 444-448.

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EXAMINER

DATE CONSIDERED

7/31/02

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